

FileViewEditToolsWindowHelp

Drafts

BRS:

BRS:

BRS:

BRS: knall

BRS: 19 21 23

BRS: 32with 33

Pending

Active

L1: (250718) (s7)icid\$4 silicat\$4)

L2: (87757) (crystal near2 (orient\$4 grow\$4 face\$2 facing state))

L3: (863838) (polysilicon polycrystalline) silicon

L4: (866667) gate

L5: (5752055) (different "same")

L6: (3305000) (different)

L7: (895) 2 near 8

L8: (8) 7 same 4

L11: (2692) 2 near 2 5

L12: (44) 11 same 4

L13: (2) 12 same 1

L14: (14) 11 same 1

L15: (8) 14 and 4

L16: (14) 8 15

Failed

Saved

(1) 09/948877

(17781) "KONINKI I IVE DUU IDS"

Browse

Queue

Clear

DBs: USPAT:US POPUB: EPO: JPO: DERWENT: ISM: TDB

Default operator: OR

Plurals

+highlight all hit terms initially

8 15

June 2004

	U	I	Investor	Document#	Issue	P	Title	Current	Current XM	Review	S	C	P	A	Image	Doc	P
1			Kohno, Yasuh	US 6180986	20010	1	Trench gate type semiconductor device with	257/173	257/174							US 6180986	
2			Iijima, Tadas	US 5803053	18990	4	Semiconductor device	257/751	257/764							US 5803053	
3			Hayakawa, Y	US 2004008	20040	2	Semiconductor device and method for manuf	257/412								US 2004008	
4			Arao, Tatsuy	US 2004007	20040	3	Semiconductor device and method for manuf	257/66								US 2004007	
5			Ellison, Alexa	US 2003007	20030	2	High resistivity silicon carbide single crystal	117/88	117/105							US 2003007	
6			Zhang, Hongy	US 2001002	20010	1	Semiconductor device and method of manufa	257/59	257/347							US 2001002	
7			Zhang, Hongy	US 6225645	20010	2	Semiconductor device and method of manufa	257/59	257/347							US 6225645	
8			Yamazaki, Sh	US 5986288	19991	1	Semiconductor device and a method of manu	257/85	257/347							US 5986288	
9			Zhang, Hongy	US 5922125	19990	1	Semiconductor device and method of manufa	117/9	117/10							US 5922125	
10			Matsubara, Y	US 5587580	18961	1	Test piece for X-ray inspection	257/48	257/384							US 5587580	

Ready

3/2/04